

EMH10 / UMH10N / IMH10A

Transistors

General purpose (dual digital transistors)

EMH10 / UMH10N / IMH10A

●Features

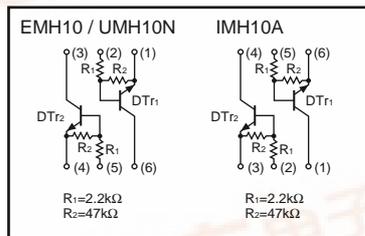
- 1) Two DTC123J chips in a EMT or UMT or SMT package.
- 2) Mounting possible with EMT3 or UMT3 or SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

●Structure

Epitaxial planar type
NPN silicon transistor
(Built-in resistor type)

The following characteristics apply to both DT_{r1} and DT_{r2}.

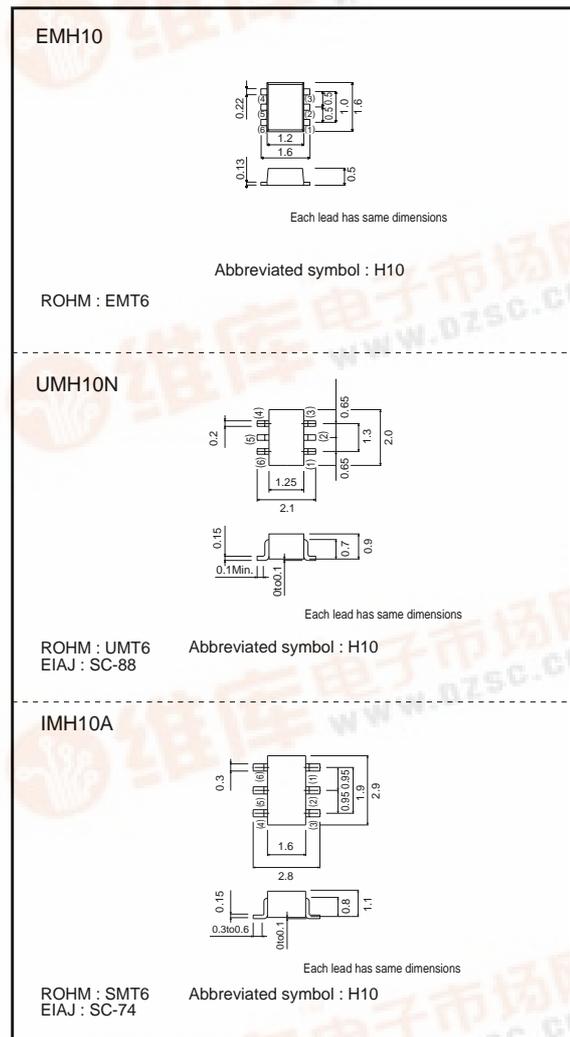
●Equivalent circuit



●Packaging specifications

| Type | Package Code Basic ordering unit (pieces) | Taping | | |
|--------|---|--------|----|------|
| | | T2R | TN | T110 |
| EMH10 | | ○ | - | - |
| UMH10N | | - | ○ | - |
| IMH10A | | - | - | ○ |

●External dimensions (Units : mm)



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● Absolute maximum ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit | | |
|---------------------|-----------------------|----------|-------------|----|----|
| Supply voltage | V _{CC} | 50 | V | | |
| Input voltage | V _{IN} | 12 | V | | |
| | | -5 | | | |
| Output current | I _O | 100 | mA | | |
| | I _{C (Max.)} | 100 | mA | | |
| Power dissipation | EMH10,UMH10N | Pd | 150 (TOTAL) | mW | *1 |
| | IMH10A | | 300 (TOTAL) | | |
| Storage temperature | T _{stg} | -55~+150 | °C | | |

*1 120mW per element must not be exceeded.
 *2 200mW per element must not be exceeded.

● Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|----------------------|--------------------------------|------|------|------|------|---|
| Input voltage | V _{I (off)} | - | - | 0.5 | V | V _{CC} =5V, I _O =100μA |
| | V _{I (on)} | 1.1 | - | - | | V _O =0.3V, I _O =5mA |
| Output voltage | V _{O (on)} | - | 0.1 | 0.3 | V | I _O /I _I =5mA/0.25mA |
| Input current | I _I | - | - | 3.6 | mA | V _I =5V |
| Output current | I _{O (off)} | - | - | 0.5 | μA | V _{CC} =50V, V _I =0V |
| DC current gain | G _I | 80 | - | - | - | V _O =5V, I _O =10mA |
| Transition frequency | f _T | - | 250 | - | MHz | V _{CE} =10mA, I _E =-5mA, f=100MHz * |
| Input resistance | R ₁ | 1.54 | 2.2 | 2.86 | kΩ | - |
| Resistance ratio | R ₂ /R ₁ | 17 | 21 | 26 | - | - |

* Transition frequency of the device

● Electrical characteristic curves

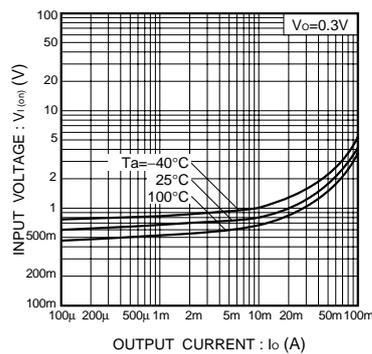


Fig.1 Input voltage vs. output current (ON characteristics)

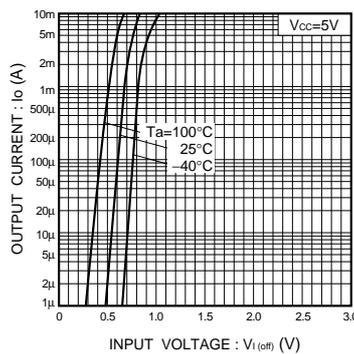


Fig.2 Output current vs. input voltage (OFF characteristics)

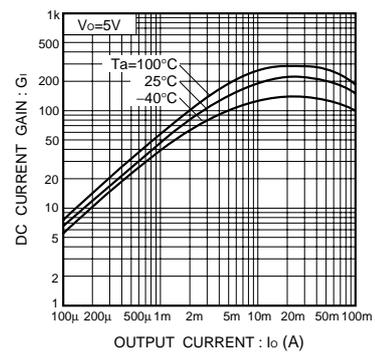


Fig.3 DC current gain vs. output current

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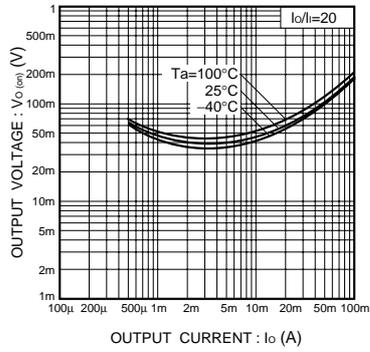


Fig.4 Output voltage vs. output current

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Datasheets for electronics components.